



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

BAT54W

SOD-323 Schottky Barrier Diode 肖特基势垒二极管

Internal Configuration & Device Marking 内部结构与产品打标

Type 型号	BAT54W
Pin 管脚	 
Mark 打标	L9

Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	30	V
Reverse Work Voltage 反向工作电压	V_{RWM}		
DC Reverse Voltage 直流反向电压	V_R		
Forward Work Current 正向工作电流	$I_F(I_O)$	200	mA
Peak Forward Current 正向峰值电流	I_{FM}	600	mA
Power dissipation 耗散功率	$P_D(T_a=25^{\circ}C)$	500	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	250	$^{\circ}C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^{\circ}C$	

Electrical Characteristics 电特性

($T_A=25^{\circ}C$ unless otherwise noted 如无特殊说明, 温度为 $25^{\circ}C$)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压($I_R=10\mu A$)	$V_{(BR)}$	30	—	V
Reverse Leakage Current 反向漏电流($V_R=25V$)	I_R	—	2	μA
Forward Voltage($I_F=1mA$) 正向电压($I_F=100mA$)	V_F		0.32 1	V
Diode Capacitance 二极管电容($V_R=1V, f=1MHz$)	C_D	—	10	pF
Reverse Recovery Time 反向恢复时间	T_{rr}	—	5	nS



■ Typical Characteristic Curve 典型特性曲线

Fig.1 Forward Current Derating Curve

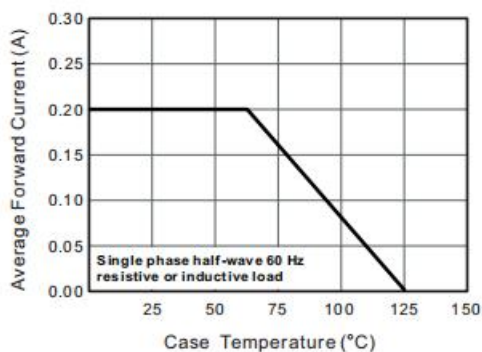


Fig.2 Typical Reverse Characteristics

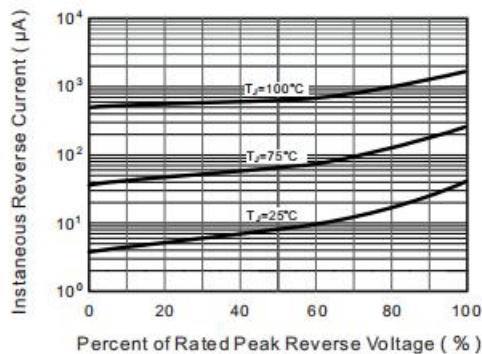


Fig.2 TYPICAL FORWARD VOLTAGE

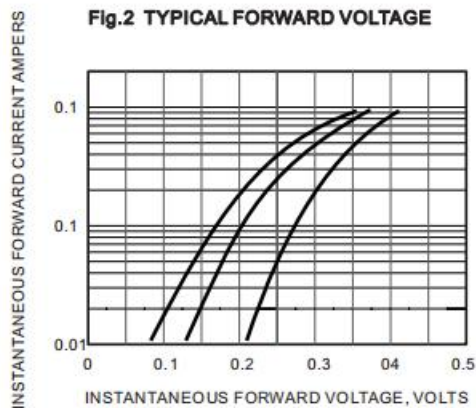


Fig.4 Typical Junction Capacitance

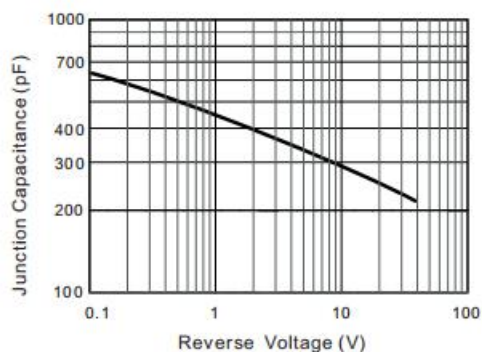
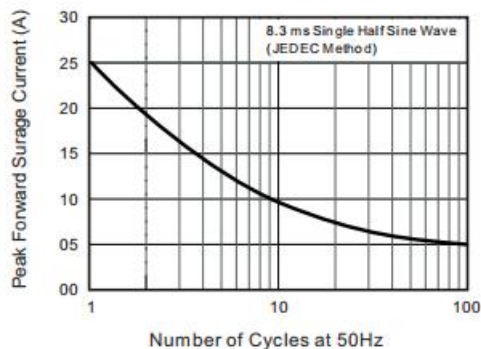


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current



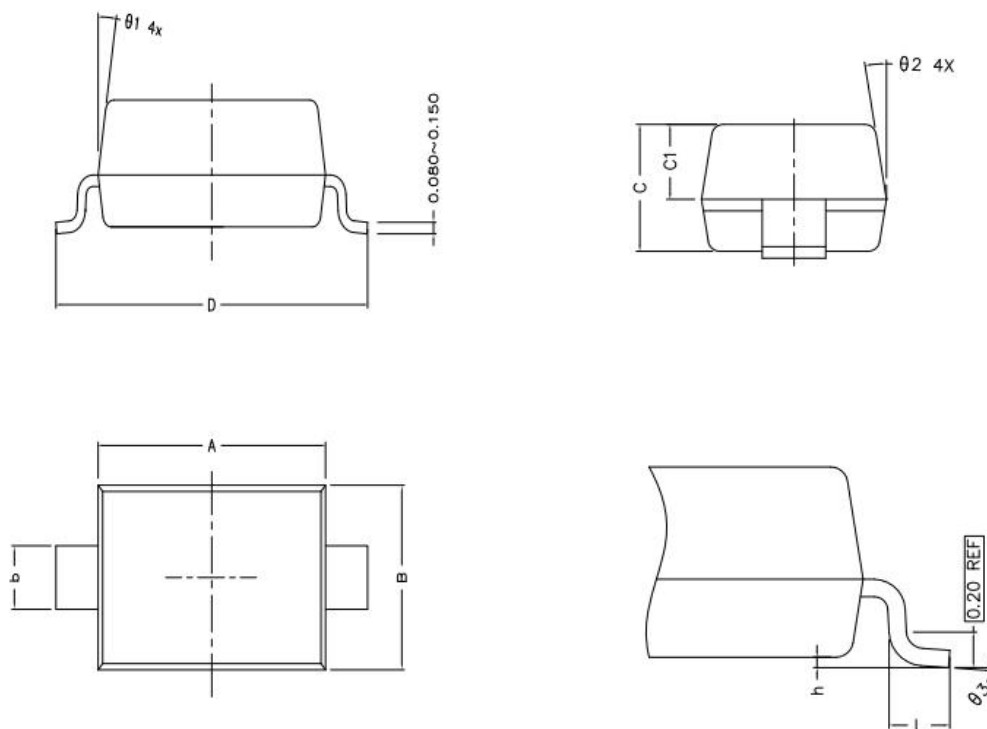


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■Dimension 外形封装尺寸



COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A	2.600	2.700	2.800
B	1.500	1.600	1.700
C	1.050	1.100	1.150
C1	0.600	0.650	0.700
D	3.550	3.700	3.850
L	0.250	0.350	0.450
h	0.010	0.050	0.100
b	0.450	0.550	0.650
$\theta 1$	9° TYPE		
$\theta 2$	9° TYPE		
$\theta 3$	0° ~ 7°		